

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	85	(hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
L2	115	HfSiON or "HfSiON" or Hf-Si-O-N	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
L3	87	(hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
L4	118	HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
L5	90	Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
L6	186	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30

L7	187	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
L8	187	L1 or L2 or L3 or L4 or L5 or L6 or L7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
L9	1479532	spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:31
L10	163754	((high\$3 or larg\$2 or big\$4) near3 (constant\$1 or dielectric\$1)) or high-dielectric\$1 or high-K or "high-K" or (high adj (K or "K")) or (high adj dielectric adj constant\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:31
L11	5726	(high\$3 or larg\$2 or big\$4) near3 (permittivity or permittivities)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:31
L12	166780	L10 or L11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:31
L13	9291	dielectric with constant\$1 with (great\$3 or high\$4 or big\$3) with (oxide\$1 or dioxide\$1 or SiO2 or "SiO2" or "SiO.sub.2" or "Si O.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:33

L14	167491	12 or 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:33
L15	1479532	spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:33
L16	36449	L15 near8 (oxide\$1 or dioxide\$1 or SiO2 or "SiO2" or "SiO.sub.2" or "Si O.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:54
L17	20163	L15 near8 (nitride\$1 or SiN or "SiN" or Si3N4 or "Si3N4" or "Si. sub.3N.sub.4" or "Si.sub.3 N.sub. 4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:54
L18	12957	L16 and L17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:52
L30	167491	10 or 11 or 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:53
L31	36449	9 near8 (oxide\$1 or dioxide\$1 or SiO2 or "SiO2" or "SiO.sub.2" or "Si O.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:54
L32	20163	9 near8 (nitride\$1 or SiN or "SiN" or Si3N4 or "Si3N4" or "Si.sub.3N. sub.4" or "Si.sub.3 N.sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:55

L33	2261	31 and 32 and 12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:56
L34	1874	12 with 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:56
L35	465	34 and 31 and 32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:58
L36	12	35 and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:58
L37	654	12 with (cap or caps or capping or capping or caped or capped or capings or cappings)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 18:06
L38	59	37 and 31 and 32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 18:07
L39	10	38 and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 18:14
L40	3963	((438/303) or (438/595) or (257/288) or (257/336) or (257/344) or (257/408)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/14 18:21
L41	107	40 and 34	US-PGPUB; USPAT	OR	OFF	2005/03/14 18:18
L43	4149	((438/303) or (438/595) or (257/288) or (257/336) or (257/344) or (257/408) or (257/900)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/14 18:21

L44	112	43 and 34	US-PGPUB; USPAT	OR	OFF	2005/03/14 18:22
S1	27	(hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:03
S2	1	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) with cap\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/11 11:10
S3	1	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) same cap\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/11 11:11
S4	970351	spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:04
S5	0	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) same (spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/11 11:13
S6	11	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) and (spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/11 11:13
S7	11	HfSiON or "HfSiON" or Hf-Si-O-N	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:05
S8	1	(HfSiON or "HfSiON" or Hf-Si-O-N) with ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/11 11:35
S9	4	(HfSiON or "HfSiON" or Hf-Si-O-N) same ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/11 12:31
S10	1	("6020243").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/11/11 14:23

S11	0	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N)) with (spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/11 14:24
S12	1	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N)) same (spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/11 14:24
S13	33	(hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:06
S14	34	HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O?	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:07
S15	67	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O?)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:06
S16	1016061	spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:07
S17	3619059	cap\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:07
S18	3	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O?)) with ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:10

S19	9	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O?)) same ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:16
S20	45	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O?)) and ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:16
S21	36	Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:08
S22	1	(Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))) with ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:57
S23	1	(Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))) same ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:58
S24	0	((Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))) and ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5)) NOT (((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O?)) and ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 10:59

S25	22	(Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))) and ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 11:01
S26	70	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 11:01
S27	108538	gate near3 (dielectric or insulat\$5 or isolat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 11:02
S28	15857	(gate near3 (dielectric or insulat\$5 or isolat\$5)) with ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 11:03
S29	19	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))))) and ((gate near3 (dielectric or insulat\$5 or isolat\$5) with ((spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)) or cap\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 11:03
S30	61	(hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/13 16:06
S31	61	(hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:54



S32	1052604	spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:00
S33	66	HfSiON or "HfSiON" or Hf-Si-O-N	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:55
S34	63	(hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:06
S35	69	HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:57
S36	64	Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:57
S37	124	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:58

S38	3	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))))) with (spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:14
S39	9	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))))) with cap\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:13
S40	6	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))))) same (spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:11

S41	16	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))))) same cap\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:13
S42	0	((((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride)))))) with liner\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:15
S43	40177	(high\$3 adj dielectric\$1) or high-dielectric\$1 or high-K or "high-K" or (high adj (K or "K")) or (high adj dielectric adj constant\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:37
S44	851	((high\$3 adj dielectric\$1) or high-dielectric\$1 or high-K or "high-K" or (high adj (K or "K")) or (high adj dielectric adj constant\$1)) with (spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:24

S45	18	((high\$3 adj dielectric\$1) or high-dielectric\$1 or high-K or "high-K" or (high adj (K or "K")) or (high adj dielectric adj constant\$1)) with (spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1))) and (((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:19
S46	497	((high\$3 adj dielectric\$1) or high-dielectric\$1 or high-K or "high-K" or (high adj (K or "K")) or (high adj dielectric adj constant\$1)) with spacer\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/14 16:25
S47	2	("6399451"   "6661067").PN.	USPAT	OR	OFF	2004/10/14 17:07
S48	85	(hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:56
S49	113	HfSiON or "HfSiON" or Hf-Si-O-N	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:55
S50	87	(hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:56
S51	116	HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:57

S52	90	Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:57
S53	184	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:58
S54	185	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 17:59
S55	185	S48 or S49 or S50 or S51 or S52 or S53 or S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:42
S56	1478558	spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:43
S57	3	S55 with S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:03

S58	8	S55 same S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:10
S59	4	S55 with (cap or caps or capping or capping or caped or capped or capings or cappings)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 18:05
S60	12	S55 same (cap or caps or capping or capping or caped or capped or capings or cappings)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:21
S61	0	S55 with liner\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:22
S62	345	hafnium adj silicate\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:22
S63	2	S62 with S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:30
S64	1	("6602720").PN.	US-PGPUB; USPAT	OR	OFF	2005/03/09 18:28
S65	13	S62 same S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:31
S66	0	S62 with (cap or caps or capping or capping or caped or capped or capings or cappings)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:35

S67	5	S62 same (cap or caps or capping or capping or capped or capped or capings or cappings)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:35
S68	163551	((high\$3 or larg\$2 or big\$4) near3 (constant\$1 or dielectric\$1)) or high-dielectric\$1 or high-K or "high-K" or (high adj (K or "K")) or (high adj dielectric adj constant\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:41
S69	5717	(high\$3 or larg\$2 or big\$4) near3 (permittivity or permittivities)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:42
S70	166575	S68 or S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:42
S71	1336	S70 near8 S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:01
S72	12	S71 and S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:50
S73	2613	liner\$4 near3 (oxide\$1 or dioxide\$1 or SiO2 or "SiO2" or "SiO.sub.2" or "Si O.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:29
S74	1850	liner\$4 near3 (nitride\$1 or SiN or "SiN" or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:31

S75	765	S73 and S74	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 18:52
S76	1871	S70 with S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:01
S77	9266	dielectric with constant\$1 with (great\$3 or high\$4 or big\$3) with (oxide\$1 or dioxide\$1 or SiO2 or "SiO2" or "SiO.sub.2" or "Si O.sub. 2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:04
S78	138	S77 with S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:05
S79	1898	S76 or S78	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:06
S80	17	S79 and S75	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:06
S81	167285	S70 or S77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:44
S82	1898	S81 with S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:32



S83	5192	S81 same S56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:33
S84	32	S83 and S75	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/09 19:33
S85	85	(hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:42
S86	114	HfSiON or "HfSiON" or Hf-Si-O-N	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:42
S87	87	(hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:42
S88	117	HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:42
S89	90	Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:42

S90	185	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:42
S91	186	((hafnium adj silicon adj (oxynitride or oxy-nitride)) or hafnium-silicon-oxynitride) or (HfSiON or "HfSiON" or Hf-Si-O-N) or ((hafnium adj silicon adj (oxynitride\$1 or oxy-nitride\$1)) or hafnium-silicon-oxynitride\$1) or (HfSiON or "HfSiON" or Hf-Si-O-N or Hf-Si-N-O or HfSiNO or "HfSiNO" or HfSi?O?N? or HfSi?N?O? or Hf?Si?O?N?) or (Hf-SiON or "Hf-SiON" or ((Hf or hafnium) adj (SiON or (silicon adj (oxynitride or oxy-nitride))))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:42
S92	186	S85 or S86 or S87 or S88 or S89 or S90 or S91	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
S93	1479347	spacer\$1 or sidewall\$1 or side-wall\$1 or (side adj wall\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:30
S94	163735	((high\$3 or larg\$2 or big\$4) near3 (constant\$1 or dielectric\$1)) or high-dielectric\$1 or high-K or "high-K" or (high adj (K or "K")) or (high adj dielectric adj constant\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:31
S95	5726	(high\$3 or larg\$2 or big\$4) near3 (permittivity or permittivities)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:44

S96	166761	S94 or S95	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:31
S97	9286	dielectric with constant\$1 with (great\$3 or high\$4 or big\$3) with (oxide\$1 or dioxide\$1 or SiO2 or "SiO2" or "SiO.sub.2" or "Si O.sub. 2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:32
S98	167472	S96 or S97	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 11:44
S99	36442	S93 near8 (oxide\$1 or dioxide\$1 or SiO2 or "SiO2" or "SiO.sub.2" or "Si O.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:32
S10 0	20159	S93 near8 (nitride\$1 or SiN or "SiN" or Si3N4 or "Si3N4" or "Si. sub.3N.sub.4" or "Si.sub.3 N.sub. 4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:31
S10 1	12956	S99 and S100	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 17:33
S10 2	14049	S93 with (oxide\$1 or dioxide\$1 or SiO2 or "SiO2" or "SiO.sub.2" or "Si O.sub.2") with (nitride\$1 or SiN or "SiN" or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:33
S10 3	16297	S101 or S102	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:33